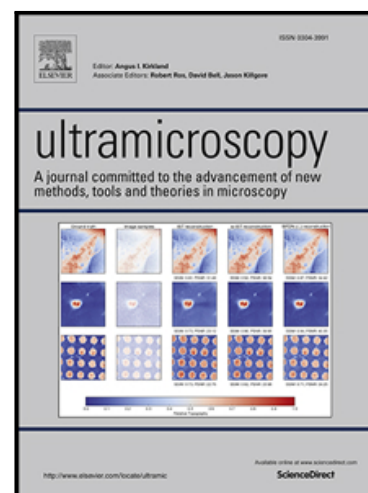


Accepted Manuscript

Atom Probe Tomography Analysis of SiGe Fins Embedded in SiO₂: Facts and Artefacts

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PII: S0304-3991(17)30029-3
DOI: [10.1016/j.ultramic.2017.04.006](https://doi.org/10.1016/j.ultramic.2017.04.006)
Reference: ULTRAM 12353



To appear in: *Ultramicroscopy*

Received date: 17 January 2017
Revised date: 11 April 2017
Accepted date: 14 April 2017

Please cite this article as: D. Melkonyan , C. Fleischmann , L. Arnoldi , J. Demeulemeester , A. Kumar , J. Bogdanowicz , F. Vurpillot , W. Vandervorst , Atom Probe Tomography Analysis of SiGe Fins Embedded in SiO₂: Facts and Artefacts, *Ultramicroscopy* (2017), doi: [10.1016/j.ultramic.2017.04.006](https://doi.org/10.1016/j.ultramic.2017.04.006)

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Highlights

- Compressed lateral dimension and oxygen penetration into the fin body are apparent.
- Causes are converging and overlapping ion trajectories due to a unique tip shape.
- A density correction algorithm rectifies the dimensional artefact.
- The Si concentration in the SiGe fin is locally overestimated by 1-2 at%.
- The artefacts depend on the ratio of the oxide/Si width in the emitter.

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